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PATENT & TRADEMARK OFFICE

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Patent

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Mary CHEN	Re: Information Disclosure Statement
Serial No.: 10/776,862	Group: not yet assigned
Filed: February 10, 2004	Examiner: not yet assigned
	Our Ref: B-4967NP 621679-8
For: "A SEMICONDUCTOR STRUCTURE FOR A HETEROJUNCTION..."	Date: August 10, 2004

Commissioner for Patents
P.O. Box 1450
Alexandria VA, 22313-1450

Sir:

In accordance with the Applicant's duty to disclose information which may be material to the examination of this application, the undersigned respectfully requests that the Examiner consider on the merits the documents listed on the enclosed Form PTO-1449 (modified) before issuing the first Office Action on the merits. We are enclosing herewith a copy of each document listed on the enclosed Form PTO-1449 (modified).

The filing of this Information Disclosure Statement (IDS) shall not be construed as a representation that a search has been made (37 C.F.R. 1.97(g)), an admission that the information cited is, or is considered to be, material to patentability, or that no other material information exists.

The Applicant believes that this IDS is being submitted before the issuance of a first Office Action on the merits and before the issuance of a Final Rejection or Notice of Allowance. Therefore, no official fees should be due; and this IDS should be considered on the merits. If this IDS is being submitted after the issuance of the first Office Action on the merits and before the issuance of a Final Rejection or Notice of Allowance, please contact the undersigned to authorize a payment of $180.00 (or any other

required amount), which is the fee set forth in 37 C.F.R. § 1.97(c), if the Examiner believes that such a fee is due in order for this IDS to be considered on the merits.

The filing of this Information Disclosure Statement shall not be construed as an admission against interest in any manner. (Notice of January 9, 1992, 1135 O.G. 13-25, at 25.)

The person making this statement is the practitioner who signs below on the basis of information supplied by an individual associated with the filing and prosecution of this application (37 C.F.R. § 1.56(c)) and on the basis of information in the practitioner's file.

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first-class mail in an envelope addressed to the "Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450", on August 10, 2004 by Shana Morda.

Respectfully submitted,

Robert Popa
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Enclosures: Form PTO-1449 (modified) (2 pages)
Copy of documents listed on Form PTO-1449 (modified)

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Form PTO-1449 (Modified) Page 1 of 2	*ATTY DOCKET NO.* B-4967NP 621679-8	*U.S. SERIAL NO.* 10/776,862
LIST OF PATENTS AND PUBLICATIONS STATEMENT	*APPLICANTS* Mary CHEN	
	FILING DATE February 10, 2004	*GROUP* not yet assigned

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	ISSUE DATE	NAME	CLASS	SUB-CLASS	FILING DATE or 102(e) DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	PUBLICATION DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO

EXAMINER	*DATE CONSIDERED*

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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Form PTO-1449 (Modified) Page 2 of 2	ATTY DOCKET NO. B-4967NP 621679-8	U.S. SERIAL NO. 10/776,862
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

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	Liu, W., "§ 3-6 Surface Current Ideality Factor," *Handbook of III-V Heterojunction Bipolar Transistors*, pp. 169-179.
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	Wu, Yu-Huei, et al., "Emitter Edge-Thinning Effect On InGaAs/InP Double-Heterostructure-Emitter Bipolar Transistor," *Jpn. J. Appl. Phys.*, Vol. 34, Part 1, No. 11, pp. 5908-5911 (1995).
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EXAMINER	DATE CONSIDERED

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